FIG. 1

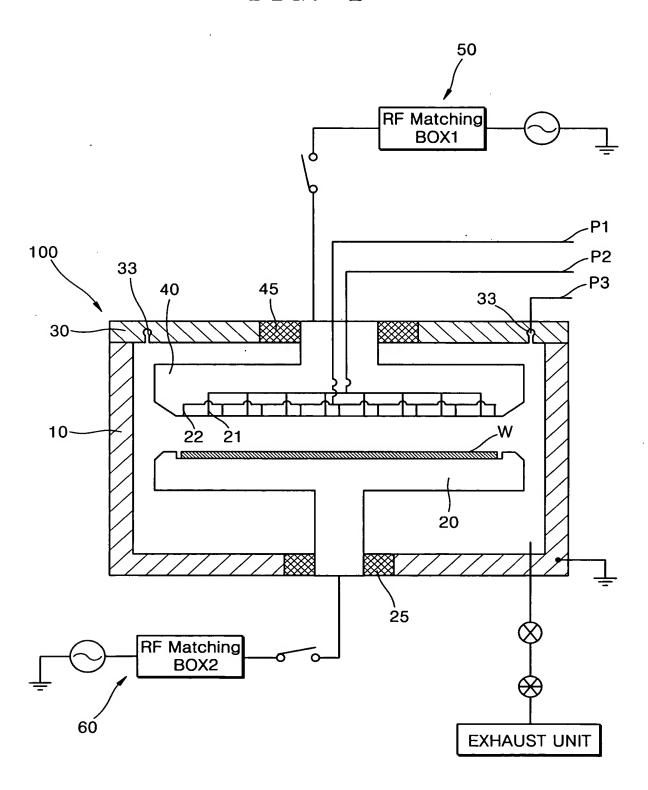


FIG. 2

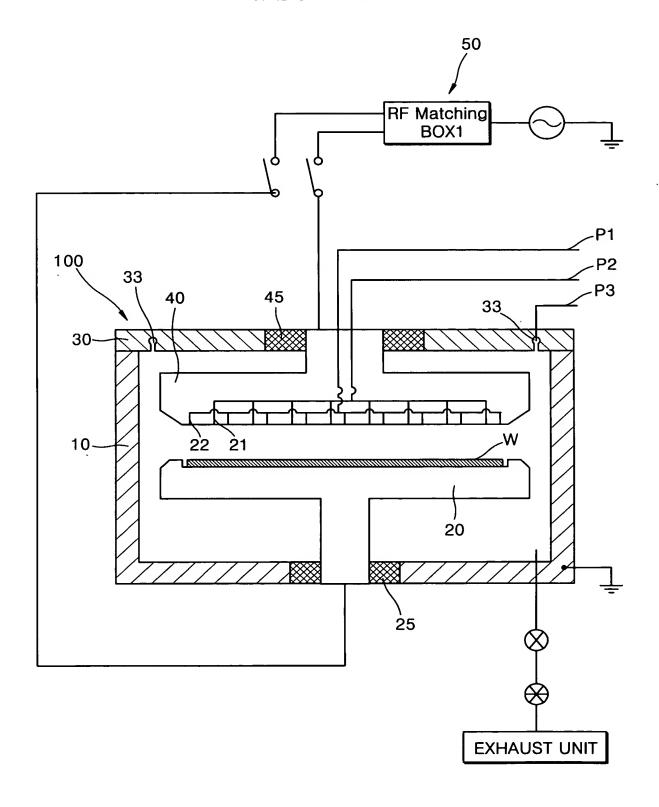


FIG. 3

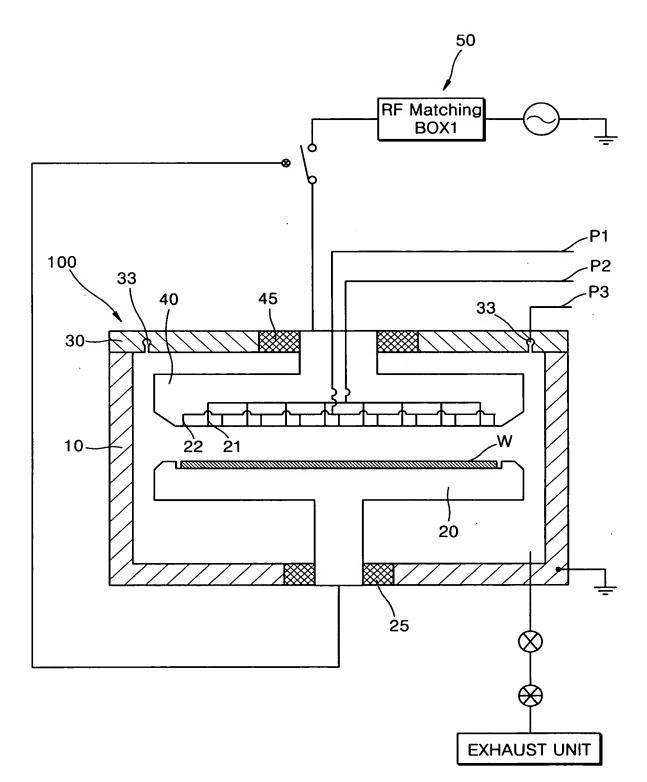
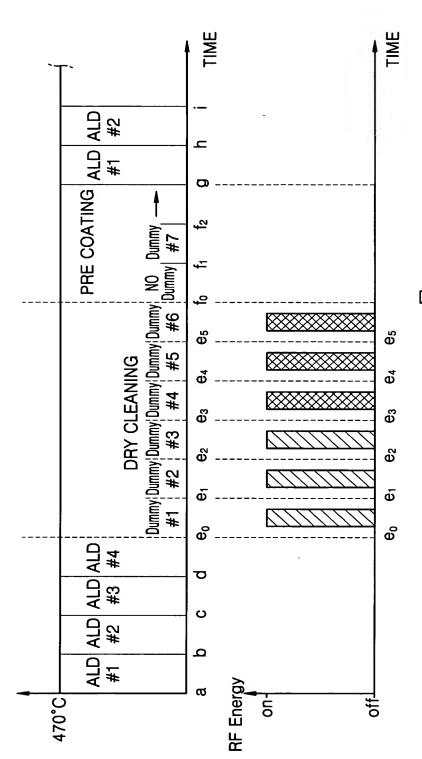


FIG. 4



S: SUPPLY RF POWER TO SHOWERHEAD

SISUPPLY RF POWER TO WAFER BLOCK

FIG. 5

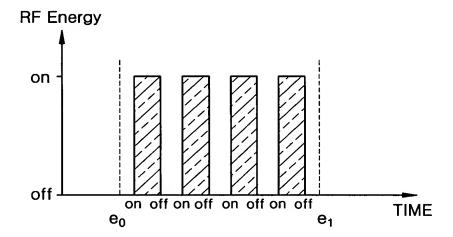


FIG. 6

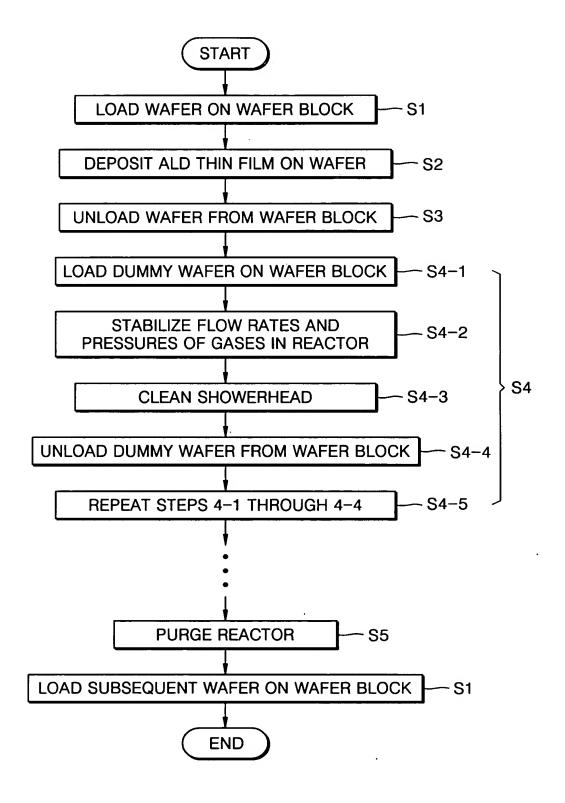


FIG. 7

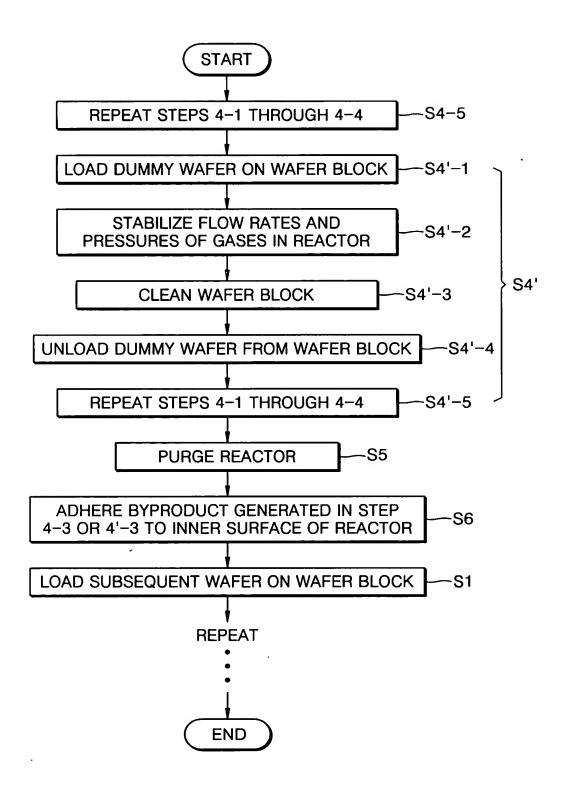


FIG. 8

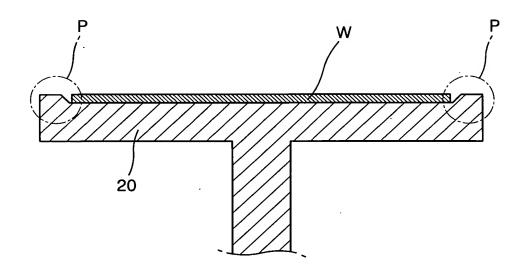


FIG. 9

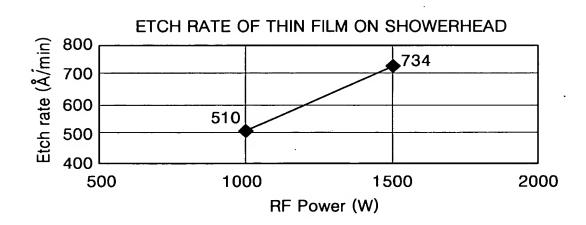


FIG. 10

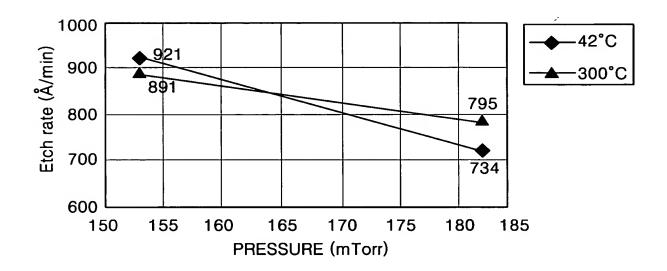


FIG. 11

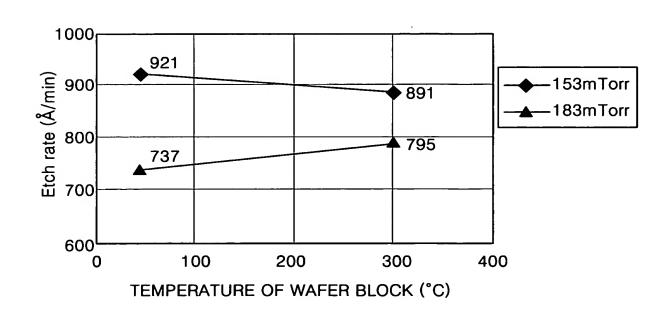


FIG. 12

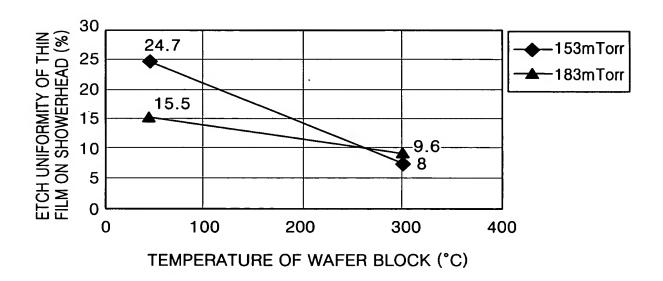


FIG. 13

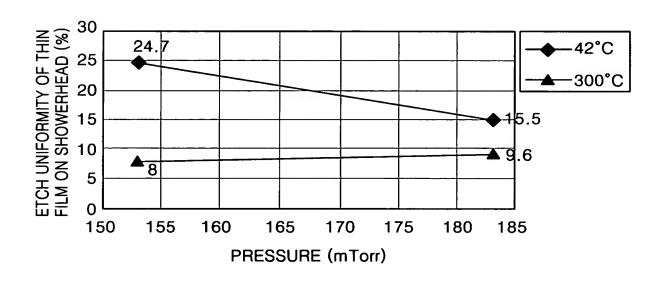
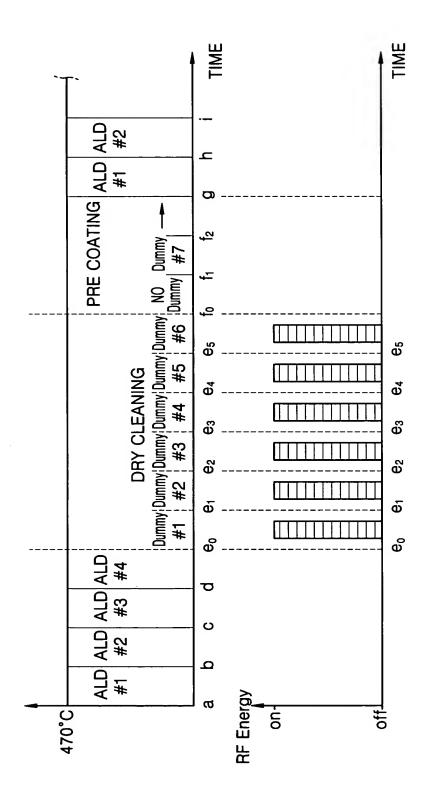


FIG. 14

TEMPERATURE OF WAFER BLOCK (°C)/ PRESSURE (mTorr)	183	153
42	734Å/min ± 15.5%	921Å/min ± 24.7%
300	795Å/min ± 9.6%	891Å/min ± 8.0%

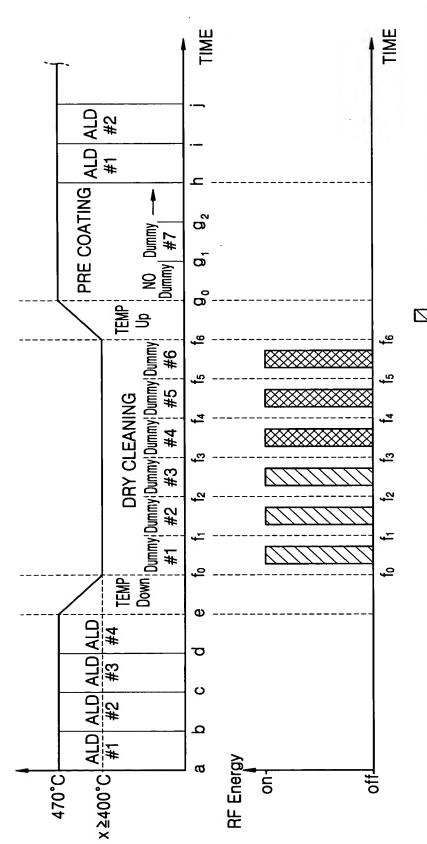
a) UNDER 183mTorr : BCl3(70sccm), Ar(30sccm),1.5KW b) UNDER 153mTorr : BCl3(50sccm), Ar(20sccm),1.5KW

FIG. 15



☐ : SIMULTANEOUSLY SUPPLY RF POWER ☐ TO SHOWERHEAD AND WAFER BLOCK

FIG. 16



SUPPLY RF POWER TO SHOWERHEAD

SUPPLY RF POWER TO WAFER BLOCK

FIG. 17

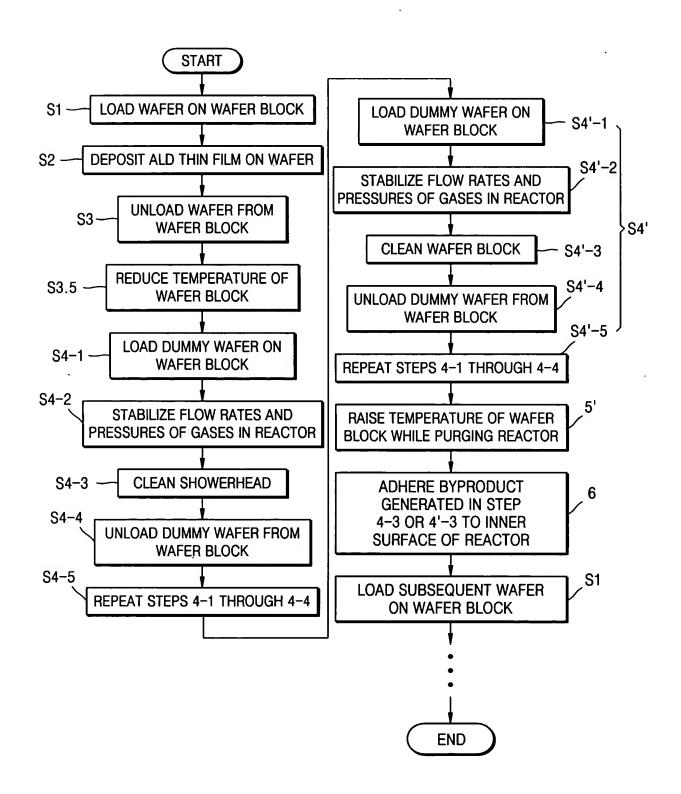
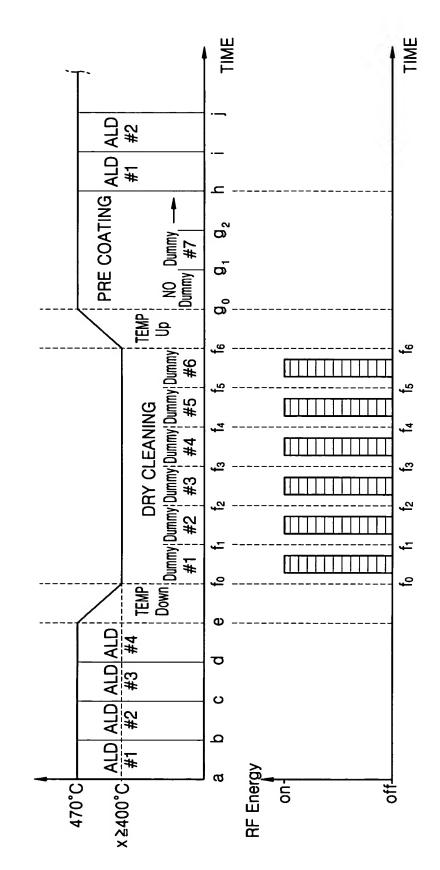


FIG. 18



☐ : SIMULTANEOUSLY SUPPLY RF POWER TO SHOWERHEAD AND WAFER BLOCK